

PSMN1R0-30YLD

N-channel 30 V, 1.0 m Ω , 300 A logic level MOSFET in LFPAK56 using NextPowerS3 Technology

21 April 2023

Product data sheet

1. General description

300 Amp Logic level gate drive N-channel enhancement mode MOSFET in LFPAK56 package. NextPowerS3 portfolio utilising Nexperia's unique "SchottkyPlus" technology delivers high efficiency, low spiking performance usually associated with MOSFETs with an integrated Schottky or Schottky-like diode but without problematic high leakage current. NextPowerS3 is particularly suited to high efficiency applications at high switching frequencies.

2. Features and benefits

- 300 Amp capability
- Avalanche rated, 100 % tested at I(as) = 190 Amps
- Ultra low Q_G, Q_{GD} and Q_{OSS} for high system efficiency, especially at higher switching frequencies
- Superfast switching with soft-recovery; s-factor > 1
- Low spiking and ringing for low EMI designs
- Unique "SchottkyPlus" technology; Schottky-like performance with < 1 μA leakage at 25 °C
- Optimised for 4.5 V gate drive
- · Low parasitic inductance and resistance
- High reliability clip bonded and solder die attach Power SO8 package; no glue, no wire bonds, qualified to 175 °C
- Wave solderable; exposed leads for optimal visual solder inspection

3. About product line

4. Applications

- On-board DC-to-DC solutions for server and telecommunications
- · Secondary-side synchronous rectification in telecommunication applications
- Voltage regulator modules (VRM)
- · Point-of-Load (POL) modules
- Power delivery for V-core, ASIC, DDR, GPU, VGA and system components
- Brushed and brushless motor control
- Power OR-ing

5. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	-	30	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	-	300	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	238	W
T _j	junction temperature			-55	-	175	°C



Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Static chara	Static characteristics							
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ Fig. 10		-	1	1.3	mΩ	
		V_{GS} = 4.5 V; I_{D} = 25 A; T_{j} = 150 °C; Fig. 10; Fig. 11		-	-	2.15	mΩ	
Dynamic ch	aracteristics			•				
Q_{GD}	gate-drain charge	I _D = 25 A; V _{DS} = 15 V; V _{GS} = 4.5 V;		-	10.9	16.35	nC	
Q _{G(tot)}	total gate charge	Fig. 12; Fig. 13		-	38.2	57.3	nC	
Source-drai	in diode							
S	softness factor	I_S = 25 A; dI_S/dt = -100 A/ μ s; V_{GS} = 0 V; V_{DS} = 15 V; Fig. 16		-	0.95	-		

^{[1] 300}A Continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, Thermal design and operating temperature.

6. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	
2	S	source		D
3	S	source		
4	G	gate		G_(□□□□)
mb	D	mounting base; connected to drain	LFPAK56; Power- SO8 (SOT669)	mbb076 S

7. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PSMN1R0-30YLD	LFPAK56; Power-SO8	plastic, single-ended surface-mounted package; 4 terminals	SOT669		

8. Marking

Table 4. Marking codes

Type number	Marking code
PSMN1R0-30YLD	1D030L

9. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	30	V

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DGR}	drain-gate voltage	25 °C ≤ T _j ≤ 175 °C; R _{GS} = 20 kΩ		-	30	V
V _{GS}	gate-source voltage			-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	238	W
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	300	Α
		V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 2</u>		-	255	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 \text{ °C}$; Fig. 3		-	1441	Α
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T _{sld(M)}	peak soldering temperature			-	260	°C
V_{ESD}	electrostatic discharge voltage	human body model		1500	-	V
Source-drain	n diode		<u>'</u>	'		
Is	source current	T _{mb} = 25 °C		-	198	Α
I _{SM}	peak source current	pulsed; t _p ≤ 10 μs; T _{mb} = 25 °C		-	1441	Α
Avalanche r	uggedness		'			_
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	I_D = 25 A; V_{sup} ≤ 30 V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped; t_p = 5.1 ms	[2]	-	2491	mJ
I _{AS}	non-repetitive avalanche current	$V_{sup} \le 30 \text{ V}; V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \text{ °C};$ $R_{GS} = 50 \Omega$	[2]	-	190	А

^{[1] 300}A Continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, Thermal design and operating temperature.

[2] Protected by 100% test

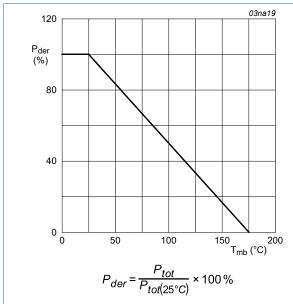
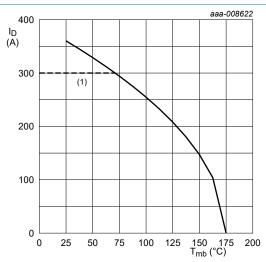
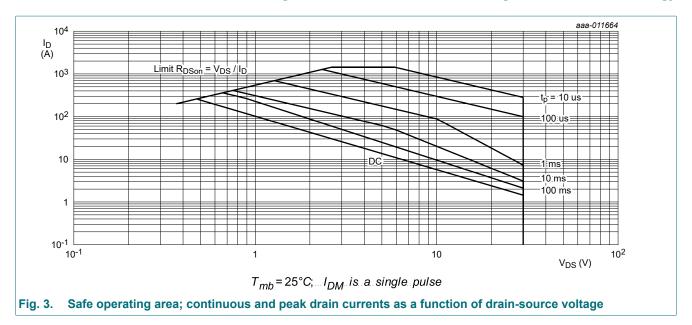


Fig. 1. Normalized total power dissipation as a function of mounting base temperature



(1) 300A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, Thermal design and operating temperature

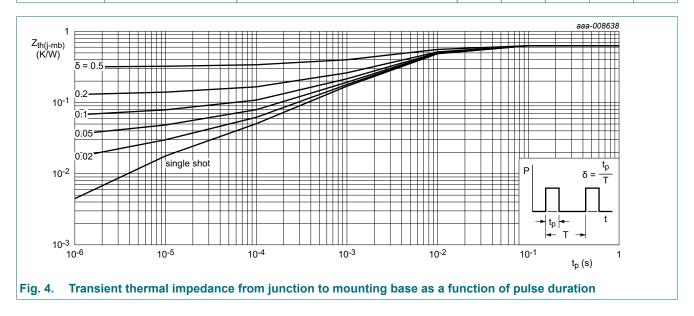
Fig. 2. Continuous drain current as a function of mounting base temperature



10. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 4	-	0.56	0.63	K/W
R _{th(j-a)} thermal resistance from junction to ambient	thermal resistance from	Fig. 5	-	50	-	K/W
	Fig. 6	-	125	-	K/W	



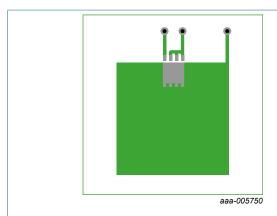


Fig. 5. PCB layout for thermal resistance junction to ambient 1" square pad; FR4 Board; 2oz copper

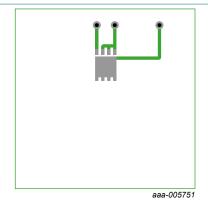


Fig. 6. PCB layout for thermal resistance junction to ambient minimum footprint;FR4 board; 2oz copper

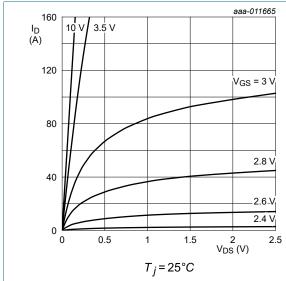
11. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static charac	teristics					
V _{(BR)DSS}	drain-source	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	30	-	-	V
	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C	27	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 2 \text{ mA}; V_{DS}=V_{GS}; T_j = 25 \text{ °C}$	1.2	1.75	2.2	V
$\Delta V_{GS(th)}/\Delta T$	gate-source threshold voltage variation with temperature	25 °C ≤ T _j ≤ 150 °C	-	-4.9	-	mV/K
I _{DSS}	drain leakage current	V _{DS} = 24 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μΑ
		V _{DS} = 24 V; V _{GS} = 0 V; T _j = 125 °C	-	2.8	-	μA
I _{GSS}	gate leakage current	V _{GS} = 16 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
		V _{GS} = -16 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ Fig. 10	-	1	1.3	mΩ
		V _{GS} = 4.5 V; I _D = 25 A; T _j = 150 °C; Fig. 10; Fig. 11	-	-	2.15	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; Fig. 10	-	0.79	1.02	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 150 °C; Fig. 10; Fig. 11	-	-	1.7	mΩ
R _G	gate resistance	f = 1 MHz	-	1.22	2.44	Ω
Dynamic cha	racteristics					
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 15 V; V _{GS} = 10 V; Fig. 12; Fig. 13	-	80.9	121.35	nC
		I _D = 25 A; V _{DS} = 15 V; V _{GS} = 4.5 V; Fig. 12; Fig. 13	-	38.2	57.3	nC
		I _D = 0 A; V _{DS} = 0 V; V _{GS} = 10 V	-	72	-	nC
	1		- I			1

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Q _{GS}	gate-source charge	I _D = 25 A; V _{DS} = 15 V; V _{GS} = 4.5 V;		-	12.5	-	nC
Q _{GS(th)}	pre-threshold gate- source charge	Fig. 12; Fig. 13		-	7.8	-	nC
Q _{GS(th-pl)}	post-threshold gate- source charge	-		-	4.7	-	nC
Q_{GD}	gate-drain charge			-	10.9	16.35	nC
V _{GS(pI)}	gate-source plateau voltage	I _D = 25 A; V _{DS} = 15 V; <u>Fig. 12</u> ; <u>Fig. 13</u>		-	2.6	-	V
C _{iss}	input capacitance	V _{DS} = 15 V; V _{GS} = 0 V; f = 1 MHz;		-	5732	8598	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 14</u>		-	2424	3636	pF
C _{rss}	reverse transfer capacitance			-	340	510	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 15 \text{ V}; R_L = 1 \Omega; V_{GS} = 4.5 \text{ V};$		-	32.4	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega$		-	44.4	-	ns
t _{d(off)}	turn-off delay time			-	43	-	ns
t _f	fall time			-	31.7	-	ns
Q _{oss}	output charge	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}$		-	55.9	-	nC
Source-dra	in diode						
V_{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 15$		-	0.77	1.2	V
t _{rr}	reverse recovery time	$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$		-	51.8	103.6	ns
Q _r	recovered charge	V _{DS} = 15 V; <u>Fig. 16</u>	[1]	-	67.1	134.2	nC
t _a	reverse recovery rise time			-	26.5	-	ns
t _b	reverse recovery fall time			-	25.3	-	ns
S	softness factor	1		-	0.95	-	

[1] includes capacitive recovery



7. Output characteristics; drain current as a function of drain-source voltage; typical values

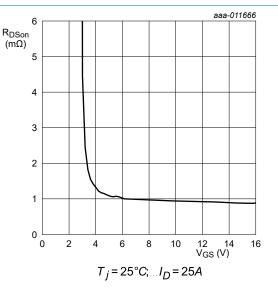
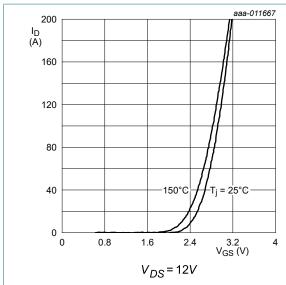


Fig. 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

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N-channel 30 V, 1.0 mΩ, 300 A logic level MOSFET in LFPAK56 using NextPowerS3 Technology



Transfer characteristics; drain current as a function of gate-source voltage; typical values

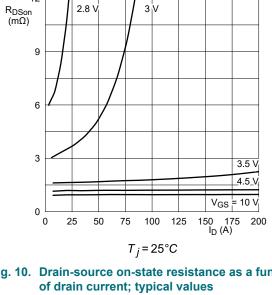


Fig. 10. Drain-source on-state resistance as a function

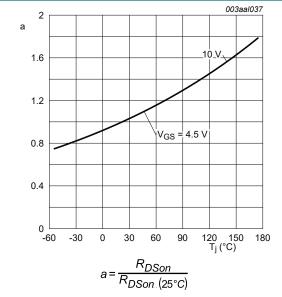


Fig. 11. Normalized drain-source on-state resistance factor as a function of junction temperature

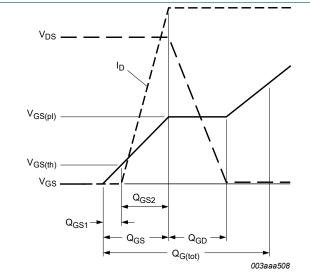


Fig. 12. Gate charge waveform definitions

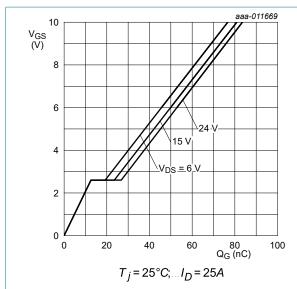


Fig. 13. Gate-source voltage as a function of gate charge; typical values

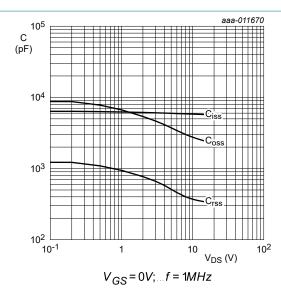


Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

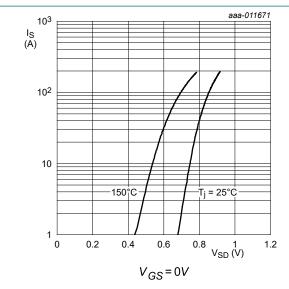


Fig. 15. Source current as a function of source-drain voltage; typical values

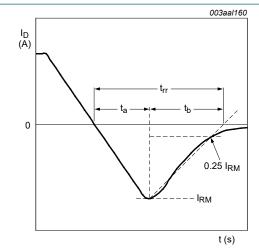


Fig. 16. Reverse recovery timing definition

12. Package outline

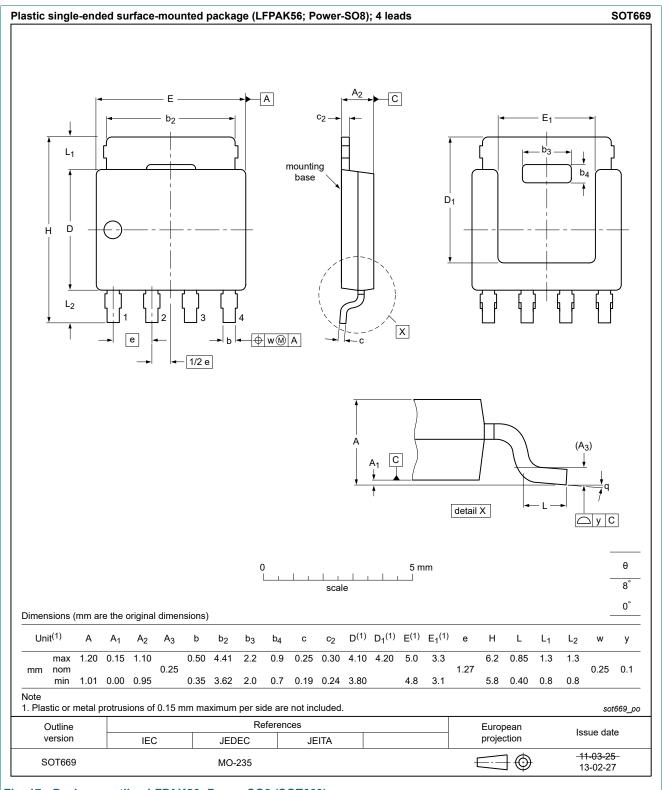
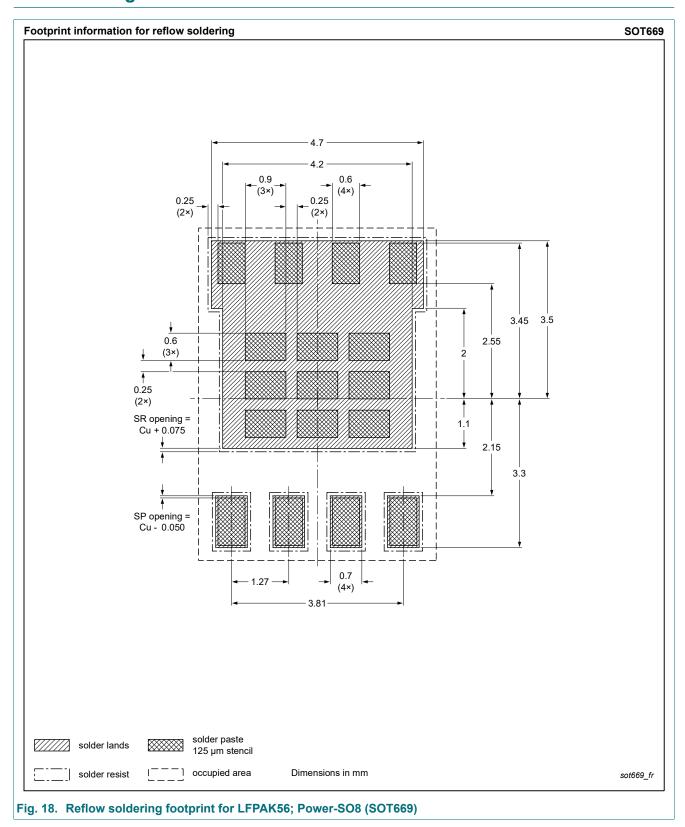
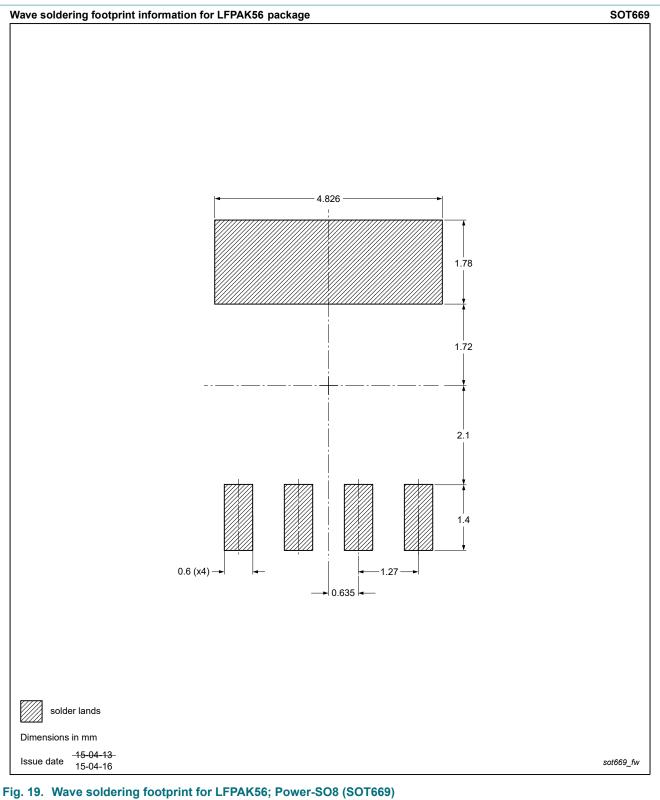


Fig. 17. Package outline LFPAK56; Power-SO8 (SOT669)

13. Soldering





14. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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For more information, please visit: http://www.nexperia.com For sales office addresses, please send an email to: salesaddresses@nexperia.com Date of release: 21 April 2023

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